This GIDEP PCN is to announce a change in the electrical characteristics for the following International Rectifier Part No listed below.

**IRHNJ67C30 (2N7598U3)**
600V 100kRad Hi-Rel Single N-Channel TID Hardened MOSFET in a SMD-0.5 package

**Electrical Characteristics @ Tj = 25°C**

- **RDS(on)** Static Drain-to-Source On-State Resistance
  @ VGS = 12V, ID = 2.1A,  *Change from 2.9 Ω to 3.1 Ω*

- **Qg** Total Gate Charge
  @ VGS =12V, ID = 3.4A, VDS = 300V,  *Change from 35nC to 52nC*

- **Qgs** Gate-to-Source Charge
  @ VGS =12V, ID = 3.4A, VDS = 300V,  *Change from 12nC to 14nC*

- **Qgd** Gate-to-Drain (‘Miller’) Charge
  @ VGS =12V, ID = 3.4A, VDS = 300V,  *Change from 15nC to 17nC*

- **td(on)** Turn-On Delay Time
  @ VDD = 300V, ID = 3.4A, VGS =12V, RG = 7.5Ω,  *Change from 18nS to 25nS*

- **tr** Rise Time
  @ VDD = 300V, ID = 3.4A, VGS =12V, RG = 7.5Ω,  *Change from 12nS to 17nS*

- **td(off)** Turn-Off Delay Time
  @ VDD = 300V, ID = 3.4A, VGS =12V, RG = 7.5Ω,  *Change from 36nS to 44nS*

Reference: IR Datasheet PD-97198